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L Number	Hits	Search Text	DB	Time stamp
-	5	(("5838041") or ("5969383")).PN.	USPAT;	2004/07/30 12:01
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
- ,	1604	(nonvolat\$4 adj2 memory) with (first adj2 second)	USPAT;	2004/07/30 12:05
			US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
	. 16	///nanyolat\$4 adi2 maman/) with (first adi2 accord) with (field	IBM_TDB USPAT;	2004/07/30 12:08
-	/ 10	(((nonvolat\$4 adj2 memory) with (first adj2 second) with (field adj effect adj transistor)) and (gate adj electrode)) and (first	US-PGPUB;	2004/07/30 12.00
		near3 region)	EPO; JPO;	
		Near 3 region)	DERWENT;	
			IBM TDB	
1_	6	((((nonvolat\$4 adj2 memory) with (first adj2 second) with	USPAT;	2004/07/30 12:10
		(((ield adj effect adj transistor)) and (gate adj electrode)) and	US-PGPUB;	2004/07/30 12.10
		(first near3 region)) and (second near3 gate adj electrode)	EPO; JPO;	
		(mot hours region)) and (second hours gute day closticus)	DERWENT;	
			IBM_TDB	
-	36	(nonvolat\$4 adj2 memory) with (first adj2 second) with (field	USPAT;	2004/07/30 12:12
		adj effect adj transistor)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	26	((nonvolat\$4 adj2 memory) with (first adj2 second) with (field	USPAT;	2004/08/03 11:46
		adj effect adj transistor)) and (gate adj electrode)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	36942	nonvolat\$4 adj2 memory	USPAT;	2004/08/03 13:20
			US-PGPUB;	
			EPO; JPO;	
1			DERWENT;	
1	569	(nonvolat\$4 adj2 memory) and ((first near2 gate near2	IBM_TDB	2004/08/03 12:55
-	509	electrode) same (second near2 gate near2 electrode))	USPAT;	2004/08/03 12:55
		Glectione, same (second fiearz gate fiearz electrone))	US-PGPUB; EPO; JPO;	
]			DERWENT;	
]			IBM_TDB	
-	419	((nonvolat\$4 adj2 memory) and ((first near2 gate near2	USPAT;	2004/08/03 12:54
		electrode) same (second near2 gate near2 electrode))) and	US-PGPUB;	
		((first or second) near4 region)	EPO; JPO;	
		, , ,	DERWENT;	
			IBM_TDB	
 -	52	((nonvolat\$4 adj2 memory) and ((first near2 gate near2	USPĀT;	2004/08/03 12:34
]		electrode) same (second near2 gate near2 electrode))) and	US-PGPUB;	
		((first or second) near4 region near4 (p adj type))	EPO; JPO;	
j			DERWENT;	
	_	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	IBM_TDB	
-	2	((nonvolat\$4 adj2 memory) and ((first near2 gate near2	USPAT;	2004/08/03 13:14
		electrode) same (second near2 gate near2 electrode))) and	US-PGPUB;	
		((first or second) near4 region near4 (first adj type))	EPO; JPO;	
			DERWENT;	
	274	((nanyolate) adi2 mamani) and ((first nano nata nano	IBM_TDB	0004/00/00 40 50
-	371	((nonvolat\$4 adj2 memory) and ((first near2 gate near2	USPAT;	2004/08/03 12:56
		electrode) same (second near2 gate near2 electrode))) and	US-PGPUB;	
		((first or second) near2 region)	EPO; JPO;	
			DERWENT; IBM_TDB	
			IDINI_I DR	

-	515	(nonvolat\$4 adj2 memory) and ((first near2 gate near2	USPAT;	2004/08/03 12:55
		electrode) with (second near2 gate near2 electrode))	US-PGPUB; EPO; JPO; DERWENT;	
_ [515	((nonvolat\$4 adj2 memory) and ((first near2 gate near2	IBM_TDB USPAT;	2004/08/03 12:55
		electrode) with (second near2 gate near2 electrode))) and ((first near2 gate near2 electrode) with (second near2 gate near2 electrode))	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
- 344	((nonvolat\$4 adj2 memory) and ((first near2 gate near2 electrode) with (second near2 gate near2 electrode))) and	USPAT; US-PGPUB;	2004/08/03 13:08	
		((first or second) near2 region)	EPO; JPO; DERWENT; IBM_TDB	
- 344	(((nonvolat\$4 adj2 memory) and ((first near2 gate near2 electrode) with (second near2 gate near2 electrode))) and ((first or second) near2 region)) and ((first or second) field adj	USPAT; US-PGPUB; EPO; JPO;	2004/08/03 13:09	
	effect)	DERWENT; IBM_TDB		
-	2	((((nonvolat\$4 adj2 memory) and ((first near2 gate near2 electrode) with (second near2 gate near2 electrode))) and ((first or second) near2 region)) and ((first or second) field adjeffect)) and ((first or second) near4 region near4 ((first or	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/08/03 13:18
- 0	second) adj type)) ((nonvolat\$4 adj2 memory) and ((first near2 gate near2 electrode) with (second near2 gate near2 electrode))) and	IBM_TDB USPAT; US-PGPUB;	2004/08/03 13:19	
		(((first or second) adj region) near4 ((first or second) adj type))	EPO; JPO; DERWENT; IBM_TDB	
-	1037	(nonvolat\$4 adj2 memory) and (charge adj storage)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/08/03 14:20
- 1037	(nonvolat\$4 adj2 memory) and (charge adj storage)	IBM_TDB USPAT; US-PGPUB;	2004/08/03 14:20	
		·	EPO; JPO; DERWENT; IBM_TDB	
	(nonvolat\$4 adj2 memory) and (charge adj storage)	USPAT; US-PGPUB; EPO; JPO;	2004/08/03 14:49	
-	0	257/257,316,319,321,324,326,315,311,322,326.ccls. and	DERWENT; IBM_TDB USPAT;	2004/08/03 14:53
		438/258,592,182,257-267,736,738,592 and ((first or second) adj gate adj electrode)	US-PGPUB; EPO; JPO; DERWENT;	
-	1	(257/257,316,319,321,324,326,315,311,322,326.ccls. and 438/258,592,182,257-267,736,738,592.ccls. and ((first or	IBM_TDB USPAT; US-PGPUB;	2004/08/03 14:56

 $257/257, 316, 319, 321, 324, 326, 315, 311, 322, 326. \, \text{ccls. and} \\$

(257/257,316,319,321,324,326,315,311,322,326.ccls. and

438/258,592,182,257-267,736,738,592.ccls. and ((first or

second) adj gate adj electrode)) and (charge adj storage)

second) adj gate adj electrode)

DERWENT; IBM_TDB

US-PGPUB; EPO; JPO;

DERWENT; IBM TDB

US-PGPUB;

EPO; JPO; DERWENT; IBM_TDB 2004/08/03 15:26

2004/08/03 15:28

USPAT;

USPAT;

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